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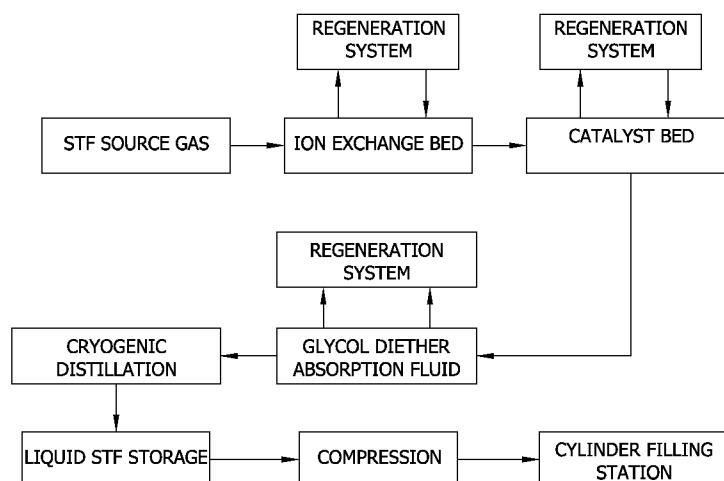
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(54) Title: PROCESSES FOR PURIFICATION OF SILICON TETRAFLUORIDE

FIG. 1



(57) Abstract: Processes for purifying silicon tetrafluoride source gas by subjecting the source gas to one or more purification processes including: contacting the silicon tetrafluoride source gas with an ion exchange resin to remove acidic contaminants, contacting the silicon tetrafluoride source gas with a catalyst to remove carbon monoxide, by removal of carbon dioxide by use of an absorption liquid, and by removal of inert compounds by cryogenic distillation; catalysts suitable for removal of carbon monoxide from silicon tetrafluoride source gas and processes for producing such catalysts.

WO 2009/042415 A2



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